

## ±3-A HIGH-EFFICIENCY H-BRIDGE (REQUIRES EXTERNAL PWM)

### FEATURES

- ±3-A Maximum Output Current
- Requires External PWM From DC to 1 MHz With TTL-Compatible Voltages for High and Low
- Low Supply Voltage Operation: 2.8 V to 5.5 V
- High Efficiency Generates Less Heat
- Over-Current and Thermal Protection
- Fault Indicators for Over-Current, Thermal and Under-Voltage Conditions
- 9×9 mm PowerPAD™ Quad Flatpack or 5×5 mm MicroStar Junior™ Packages

### APPLICATIONS

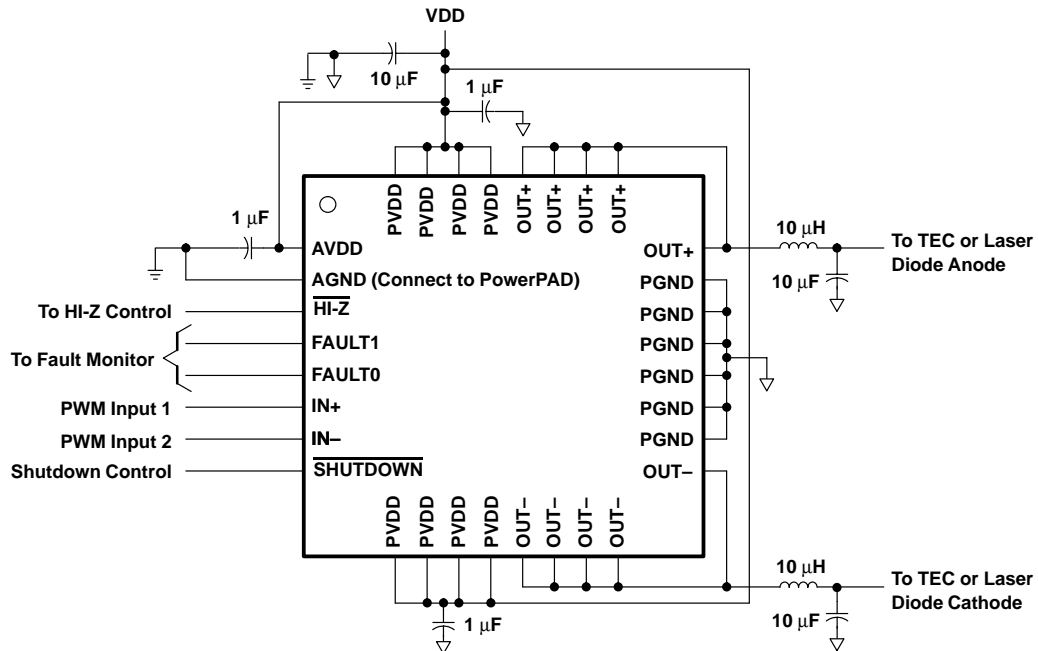
- Thermoelectric Cooler (TEC) Driver
- Laser Diode Biasing

### DESCRIPTION

The DRV592 is a high-efficiency, high-current H-bridge ideal for driving a wide variety of thermoelectric cooler elements in systems powered from 2.8 V to 5.5 V. Low output stage on-resistance significantly decreases power dissipation in the device.

The DRV592 may be driven from any external PWM generator such as a DSP, a microcontroller, or a FPGA. The frequency may vary from dc (i.e., on or off) to 1 MHz. The inputs are compatible with TTL logic levels.

The DRV592 is internally protected against thermal and current overloads. Logic-level fault indicators signal when the junction temperature has reached approximately 130°C to allow for system-level shutdown before the amplifier's internal thermal shutdown circuitry activates. The fault indicators also signal when an over-current event has occurred. If the over-current circuitry is tripped, the DRV592 will automatically reset.

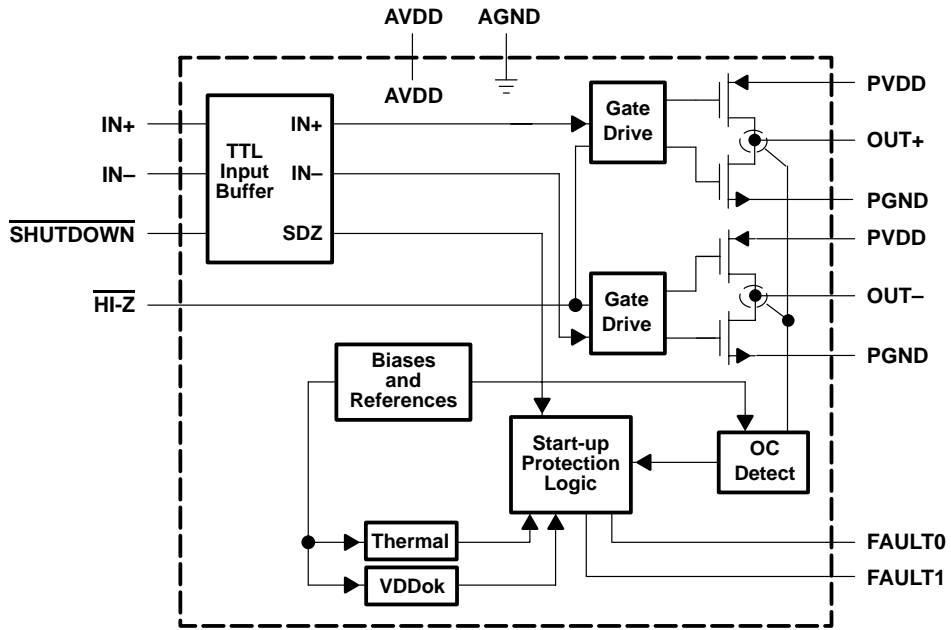


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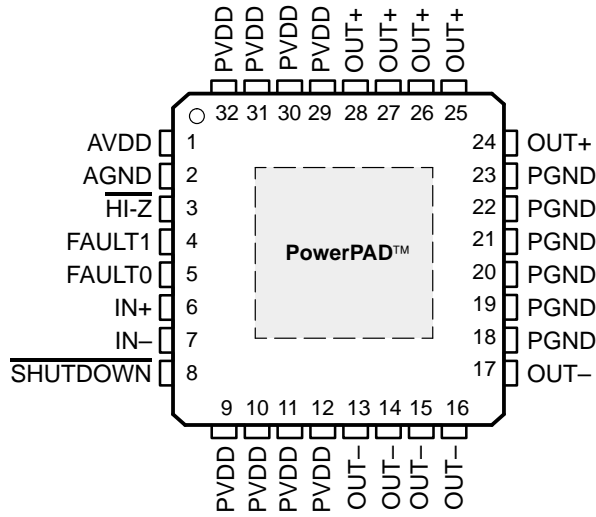
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PRODUCTION DATA information is current as of publication date. Products conform to specifications per the terms of Texas Instruments standard warranty. Production processing does not necessarily include testing of all parameters.

block diagram



VFP PACKAGE  
(TOP VIEW)



## Terminal Functions

TERMINAL NAME	NO.	I/O	DESCRIPTION
AGND	2		Analog ground
AVDD	1	I	Analog power supply
FAULT0	5	O	Fault flag 0, low when active open drain output (see application information)
FAULT1	4	O	Fault flag 1, low when active open drain output (see application information)
HI-Z	3	I	Places both outputs of the H-bridge into a high-impedance state (2 k $\Omega$ to ground) when a TTL logic low is applied to this terminal; normal operation when a TTL logic high is applied.
IN-	7	I	Negative H-bridge input
IN+	6	I	Positive H-bridge input
OUT-	13–17	O	Negative H-bridge output (5 terminals)
OUT+	24–28	O	Positive H-bridge output (5 terminals)
PGND	18–23		High-current ground (6 terminals)
PVDD	9–12, 29–32	I	High-current power supply (8 terminals)
SHUTDOWN	8	I	Places the amplifier in shutdown mode when a TTL logic low is applied to this terminal; places the amplifier in normal operation when a TTL logic high is applied

## absolute maximum ratings over operating free-air temperature (unless otherwise noted)†

Supply voltage, AVDD, PVDD	–0.3 V to 5.5 V
Input voltage, V <sub>I</sub>	–0.3 V to V <sub>DD</sub> + 0.3 V
Output current, I <sub>O</sub> (FAULT0, FAULT1)	1 mA
Continuous total power dissipation	See Dissipation Rating Table
Operating free-air temperature range, T <sub>A</sub>	–40°C to 85°C
Operating junction temperature range, T <sub>J</sub>	–40°C to 125°C
Storage temperature range, T <sub>stg</sub>	–65°C to 165°C

† Stresses beyond those listed under “absolute maximum ratings” may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under “recommended operating conditions” is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

DISSIPATION RATING TABLE

PACKAGE	$\theta_{JA}^{\ddagger}$ (°C/W)	$\theta_{JC}$ (°C/W)	T <sub>A</sub> = 25°C POWER RATING
VFP	29.4	1.2	4.1 W
GQE $^{\S}$	37.8	4.56	3.3 W

$^{\ddagger}$  This data was taken using 2 oz trace and copper pad that is soldred directly to a JEDEC standard 4-layer 3 in  $\times$  3 in PCB.

$^{\S}$  This package is in the Product Preview stage of development.

## AVAILABLE OPTIONS

T <sub>A</sub>	PACKAGED DEVICES	
	PowerPAD QUAD FLATPACK (VFP)	PLASTIC BALL GRID ARRAY MicroStar Junior (GQE)
–40°C to 85°C	DRV592VFP $^{\parallel}$	DRV592GQE

$^{\parallel}$  Tape and reel transport media is in the Product Preview stage of development

**recommended operating conditions**

		MIN	MAX	UNIT
Supply voltage, AVDD, PVDD		2.8	5.5	V
High-level input voltage, V <sub>IH</sub>	SHUTDOWN, HI-Z, IN+, IN-	2		V
Low-level input voltage, V <sub>IL</sub>	SHUTDOWN, HI-Z, IN+, IN-		0.8	V
Operating free-air temperature, T <sub>A</sub>		-40	85	°C

**electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)**

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT
V <sub>O</sub>	Voltage output (measured differentially)	V <sub>DD</sub> = 5 V	I <sub>O</sub> = ±1 A, r <sub>ds(on)</sub> = 65 mΩ		4.87		V
			I <sub>O</sub> = ±3 A, r <sub>ds(on)</sub> = 65 mΩ		4.61		
r <sub>DS(on)</sub>	Output on-resistance	V <sub>DD</sub> = 5 V, I <sub>O</sub> = 4 A, T <sub>A</sub> = 25°C	High side	25	60	95	mΩ
			Low side	25	65	95	
		V <sub>DD</sub> = 3.3 V, I <sub>O</sub> = 4 A, T <sub>A</sub> = 25°C	High side	25	80	140	mΩ
			Low side	25	90	140	
Maximum continuous current output					3		A
Output resistance in shutdown		SHUTDOWN = 0.8 V		1	2	3.5	kΩ
Switching frequency				0 (dc)		1	MHz
Status flag output pins (FAULT0, FAULT1) Fault active (open drain output)		Sinking 200 μA				0.1	V
I <sub>q</sub>	Quiescent current	V <sub>DD</sub> = 5 V	No switching	0	0.5	1.5	mA
		V <sub>DD</sub> = 3.3 V		0	0.3	1	
I <sub>q(SD)</sub>	Quiescent current in shutdown mode	SHUTDOWN = 0.8 V			0.01	50	μA

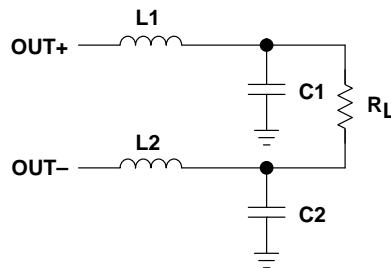
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**TYPICAL CHARACTERISTICS**
**Table of Graphs**

		FIGURE
Efficiency	vs Load resistance	2, 3
$r_{DS(on)}$ Drain-source on-state resistance	vs Supply voltage	4
	vs Free-air temperature	5
	vs Free-air temperature	6
$I_q$ Supply current	vs Switching frequency	7
PSRR Power supply rejection ratio	vs Frequency	8, 9
Closed loop response		10, 11
$I_O$ Maximum output current	vs Output voltage	12
	vs Ambient temperature	13

**test set-up for graphs**

The LC output filter used in Figures 2, 3, 8, and 9 is shown below.



L1, L2 = 10  $\mu$ H (part number: CDRH104R, manufacturer: Sumida)  
 C1, C2 = 10  $\mu$ F (part number: ECJ-4YB1C106K, manufacturer: Panasonic)

**Figure 1. LC Output Filter**

TYPICAL CHARACTERISTICS

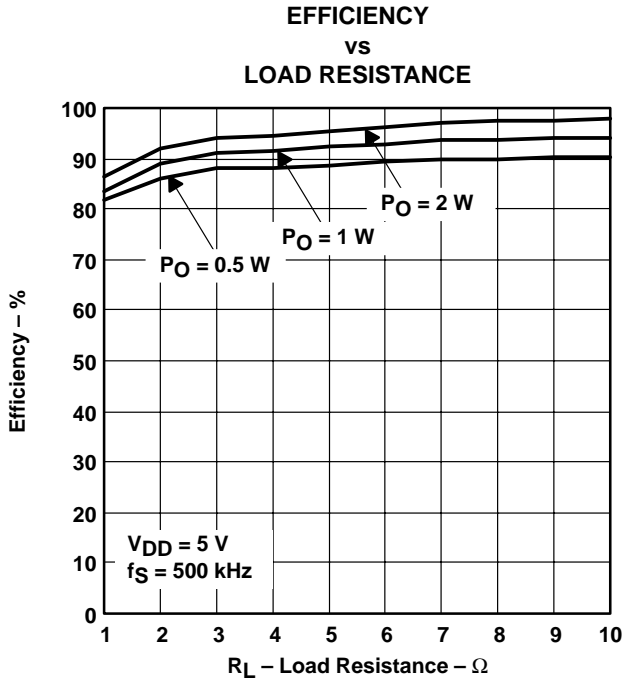


Figure 2

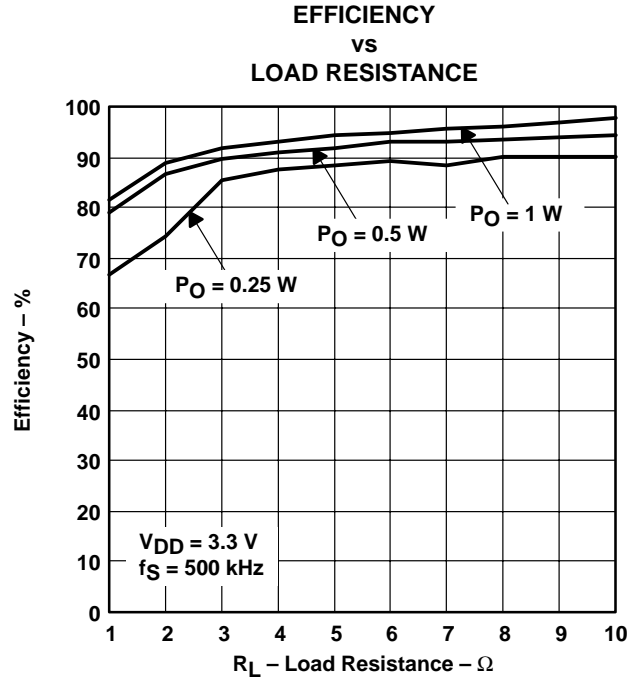


Figure 3

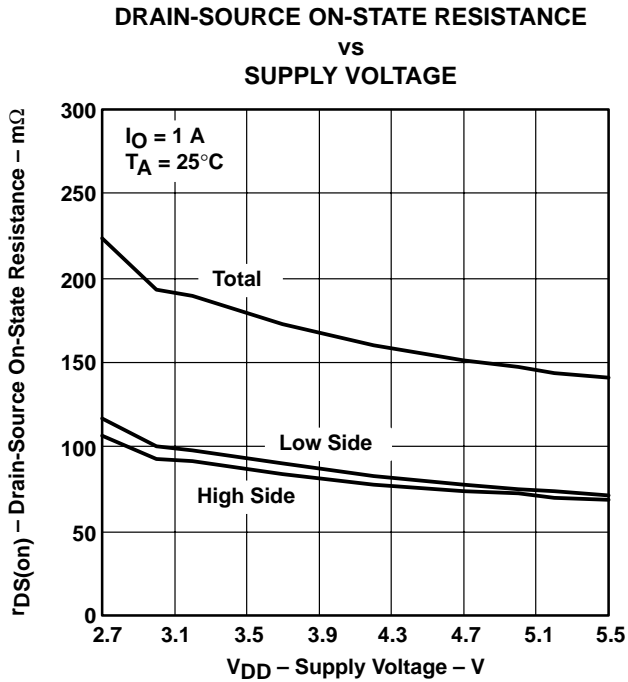


Figure 4

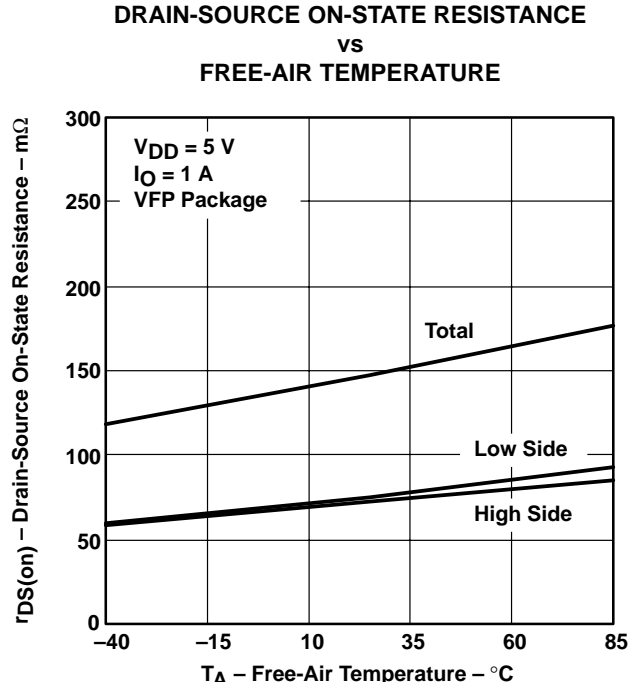


Figure 5

TYPICAL CHARACTERISTICS

DRAIN-SOURCE ON-STATE RESISTANCE  
vs  
FREE-AIR TEMPERATURE

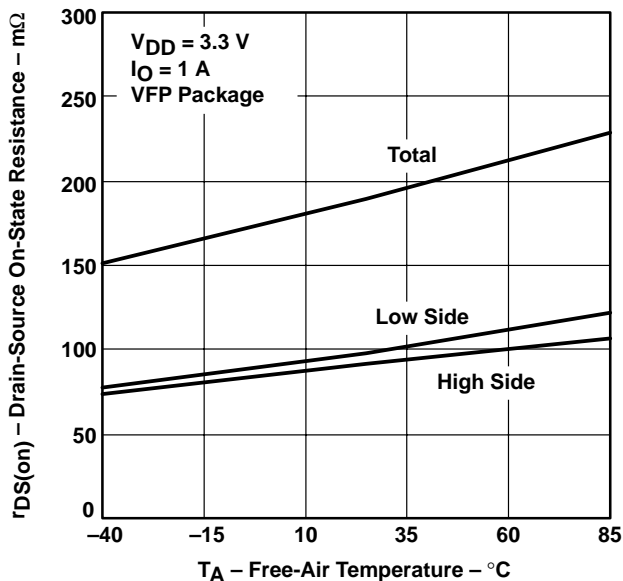


Figure 6

SUPPLY CURRENT  
vs  
SWITCHING FREQUENCY

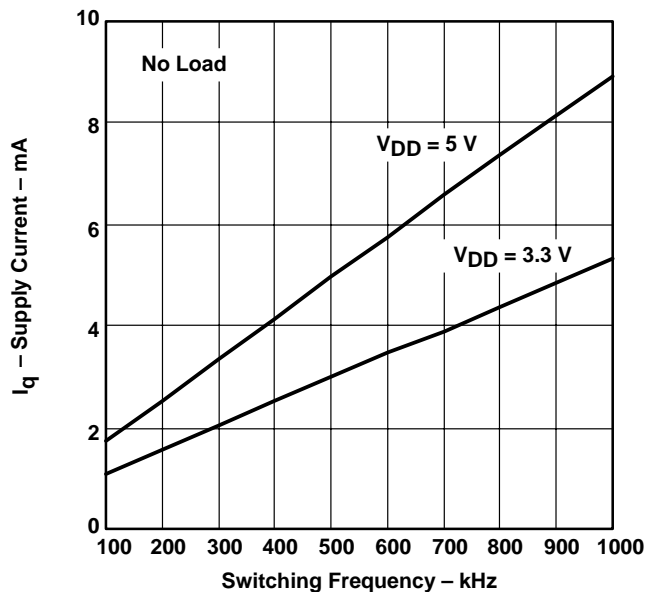


Figure 7

POWER SUPPLY REJECTION RATIO  
vs  
FREQUENCY

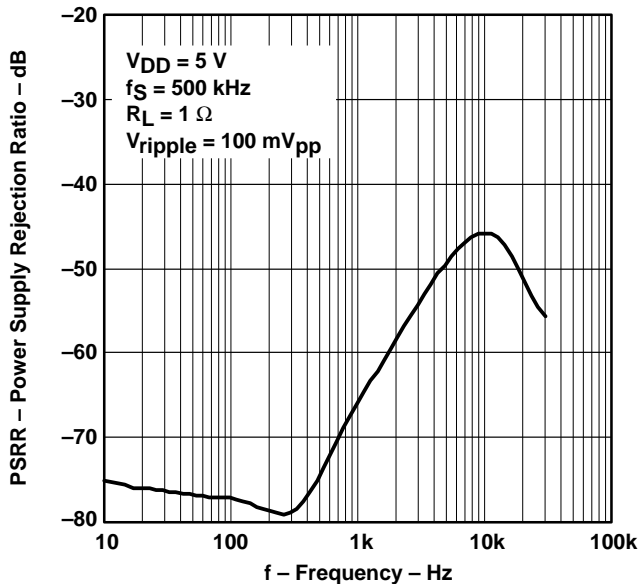


Figure 8

POWER SUPPLY REJECTION RATIO  
vs  
FREQUENCY

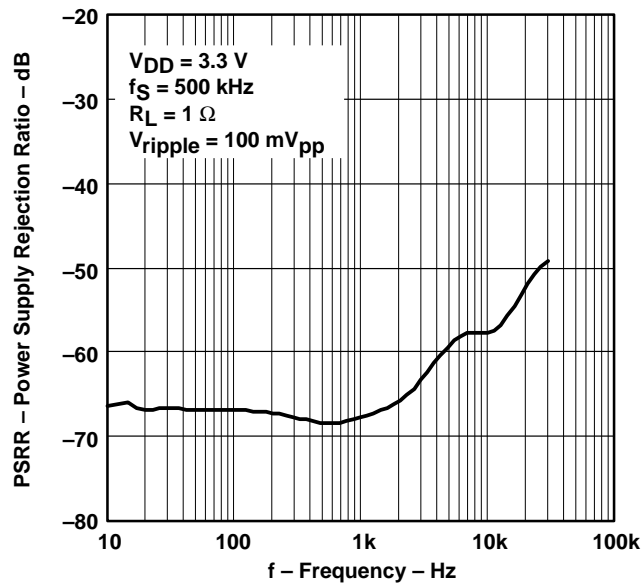


Figure 9

TYPICAL CHARACTERISTICS

MAXIMUM OUTPUT CURRENT  
vs  
OUTPUT VOLTAGE

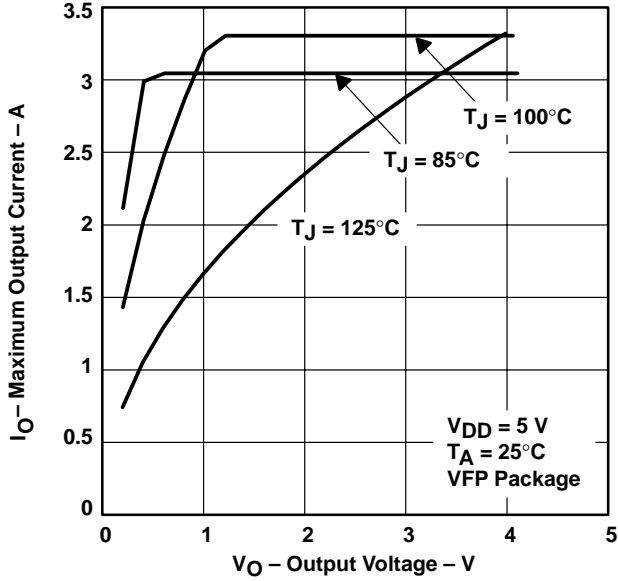


Figure 10

MAXIMUM OUTPUT CURRENT  
vs  
AMBIENT TEMPERATURE

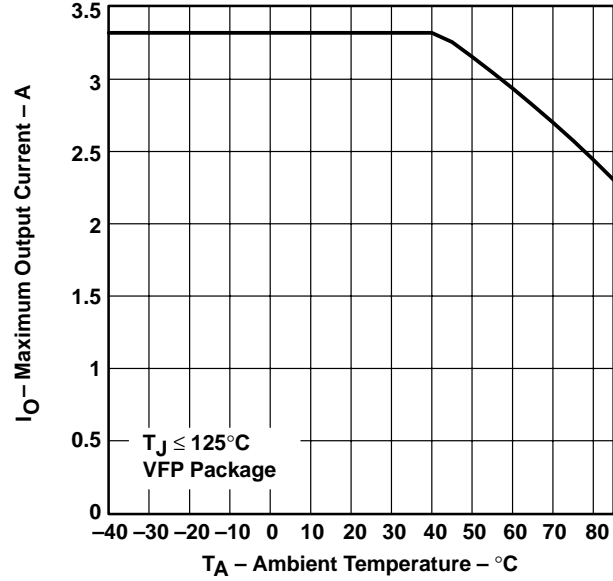


Figure 11

APPLICATION INFORMATION

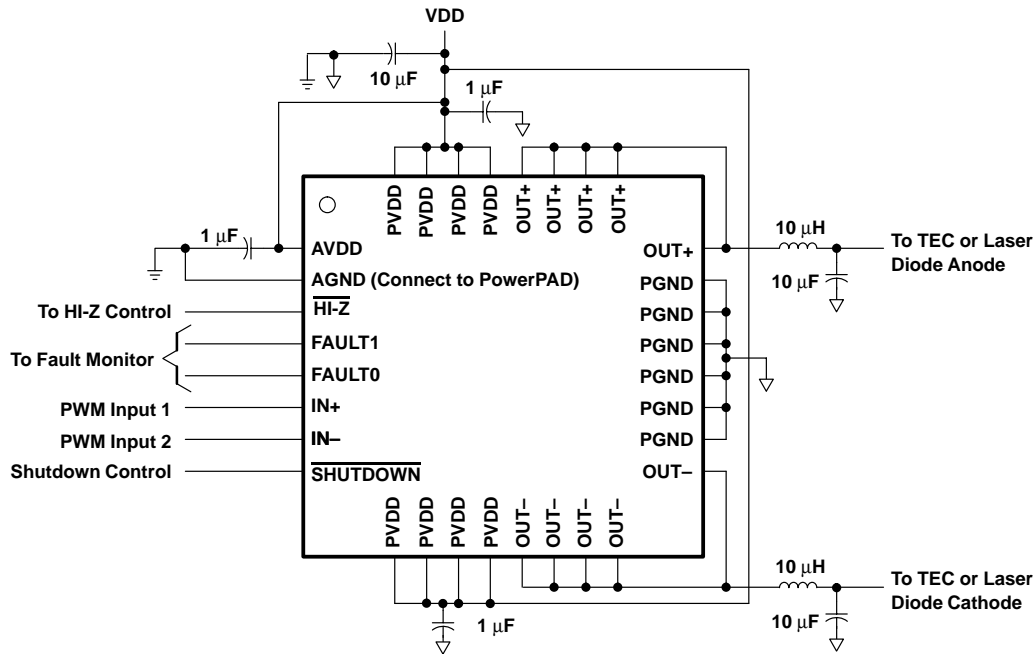


Figure 12. Typical Application Circuit

driving externally-generated PWM to the DRV592 inputs

The DRV592 may be simply viewed as a full-H-bridge, with all the gate drive and protection circuitry fully integrated, but with no internal PWM generator.

The inputs may be driven independently with a PWM signal ranging from dc to 1 MHz. The HIGH and LOW levels must be TTL compatible. For example, when a voltage 2 V or higher is applied to IN+, then OUT+ will go to VDD. If a voltage 0.8 V or lower is applied, then the output will go to ground.

Any PWM modulation scheme may be applied to the DRV592 inputs.

output filter considerations

TEC element manufacturers provide electrical specifications for maximum dc current and maximum output voltage for each particular element. The maximum ripple current, however, is typically only recommended to be less than 10% with no reference to the frequency components of the current. The maximum temperature differential across the element, which decreases as ripple current increases, may be calculated with the following equation:

$$\Delta T = \frac{1}{(1 + N^2)} \times \Delta T_{max} \tag{1}$$

Where:

$\Delta T$  = actual temperature differential

$\Delta T_{max}$  = maximum temperature differential (specified by manufacturer)

N = ratio of ripple current to dc current

**APPLICATION INFORMATION**

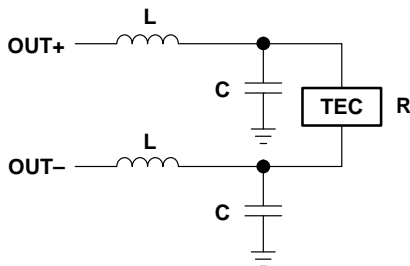
**output filter considerations (continued)**

According to this relationship, a 10% ripple current reduces the maximum temperature differential by 1%. An LC network may be used to filter the current flowing to the TEC to reduce the amount of ripple and, more importantly, protect the rest of the system from any electromagnetic interference (EMI).

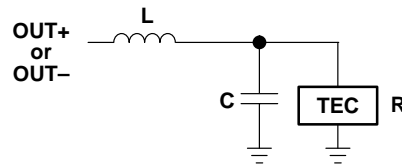
**filter component selection**

The LC filter, which may be designed from two different perspectives, both described below, will help estimate the overall performance of the system. The filter should be designed for the worst-case conditions during operation, which is typically when the differential output is at 50% duty cycle. The following section serves as a starting point for the design, and any calculations should be confirmed with a prototype circuit in the lab.

Any filter should always be placed as close as possible to the DRV592 to reduce EMI.



**Figure 13. LC Output Filter**



**Figure 14. LC Half-Circuit Equivalent**

**LC filter in the frequency domain**

The transfer function for a 2<sup>nd</sup> order low-pass filter (Figures 13 and 14) is shown in equation (2):

$$H_{LP}(j\omega) = \frac{1}{-\left(\frac{\omega}{\omega_0}\right)^2 + \frac{1}{Q} \frac{j\omega}{\omega_0} + 1} \tag{2}$$

$$\omega_0 = \frac{1}{\sqrt{LC}}$$

Q = quality factor

$\omega$  = DRV592 switching frequency

The resonant frequency for the filter is typically chosen to be at least one order of magnitude lower than the switching frequency. Equation (2) may then be simplified to give the following magnitude equation (3). These equations assume the use of the filter in Figure 13.

$$|H_{LP}|_{dB} = -40 \log \left( \frac{f_s}{f_0} \right) \tag{3}$$

$$f_0 = \frac{1}{2\pi\sqrt{LC}}$$

$f_s$  = 500 kHz (DRV592 switching frequency)

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**APPLICATION INFORMATION**
**LC filter in the frequency domain (continued)**

If  $L=10\ \mu\text{H}$  and  $C=10\ \mu\text{F}$ , the resonant frequency is 15.9 kHz, which corresponds to  $-60\ \text{dB}$  of attenuation at the 500 kHz switching frequency. For  $V_{\text{DD}} = 5\ \text{V}$ , the amount of ripple voltage at the TEC element is approximately 5 mV.

The average TEC element has a resistance of  $1.5\ \Omega$ , so the ripple current through the TEC is approximately 3.4 mA. At the 3-A maximum output current of the DRV592, this 3.4 mA corresponds to 0.011% ripple current, causing less than 0.0001% reduction of the maximum temperature differential of the TEC element (see equation 1).

**LC filter in the time domain**

The ripple current of an inductor may be calculated using equation (4):

$$\Delta I_L = \frac{(V_O - V_{\text{TEC}})DT_s}{L} \quad (4)$$

$D$  = duty cycle (0.5 worst case)

$$T_s = 1/f_s$$

For  $V_O = 5\ \text{V}$ ,  $V_{\text{TEC}} = 2.5\ \text{V}$ , and  $L = 10\ \mu\text{H}$ , and a switching frequency of 500 kHz; the inductor ripple current is 250 mA. To calculate how much of that ripple current will flow through the TEC element, however, the properties of the filter capacitor must be considered.

For relatively small capacitors (less than  $22\ \mu\text{F}$ ) with very low equivalent series resistance (ESR, less than  $10\ \text{m}\Omega$ ), such as ceramic capacitors, the following equation (5) may be used to estimate the ripple voltage on the capacitor due to the change in charge:

$$\Delta V_C = \frac{\pi^2}{2} (1-D) \left(\frac{f_o}{f_s}\right)^2 V_{\text{TEC}} \quad (5)$$

$D$  = duty cycle

$f_s$  = DRV592 switching frequency

$$f_o = \frac{1}{2\pi\sqrt{LC}}$$

For  $L = 10\ \mu\text{H}$  and  $C = 10\ \mu\text{F}$ , the cutoff frequency,  $f_o$ , is 15.9 kHz. For worse case duty cycle of 0.5 and  $V_{\text{TEC}} = 2.5\ \text{V}$ , the ripple voltage on the capacitors is 6.2 mV. The ripple current may be calculated by dividing the ripple voltage by the TEC resistance of  $1.5\ \Omega$ , resulting in a ripple current through the TEC element of 4.1 mA. Note that this is similar to the value calculated using the frequency domain approach.

For larger capacitors (greater than  $22\ \mu\text{F}$ ) with relatively high ESR (greater than  $100\ \text{m}\Omega$ ), such as electrolytic capacitors, the ESR dominates over the charging-discharging of the capacitor. The following simple equation (6) may be used to estimate the ripple voltage:

$$\Delta V_C = \Delta I_L \times R_{\text{ESR}} \quad (6)$$

$\Delta I_L$  = inductor ripple current

$R_{\text{ESR}}$  = filter capacitor ESR

**APPLICATION INFORMATION**

**LC filter in the time domain (continued)**

For a 100  $\mu$ F electrolytic capacitor, an ESR of 0.1  $\Omega$  is common. If the 10  $\mu$ H inductor is used, delivering 250 mA of ripple current to the capacitor (as calculated above), then the ripple voltage is 25 mV. This is over ten times that of the 10  $\mu$ F ceramic capacitor, as ceramic capacitors typically have negligible ESR.

For worst case conditions, the on-resistance of the output transistors has been ignored to give the maximum theoretical ripple current. In reality, the voltage drop across the output transistors decreases the maximum  $V_O$  as the output current increases. It can be shown using equation (4) that this decreases the inductor ripple current, and therefore the TEC ripple current.

**power supply decoupling**

To reduce the effects of high-frequency transients or spikes, a small ceramic capacitor, typically 0.1  $\mu$ F to 1  $\mu$ F, should be placed as close to each set of PVDD pins of the DRV592 as possible. For bulk decoupling, a 10  $\mu$ F to 100  $\mu$ F tantalum or aluminum electrolytic capacitor should be placed relatively close to the DRV592.

**SHUTDOWN operation**

The DRV592 includes a shutdown mode that disables the outputs and places the device in a low supply current state. The SHUTDOWN pin may be controlled with a TTL logic signal. When SHUTDOWN is held high, the device operates normally. When SHUTDOWN is held low, the device is placed in shutdown. The SHUTDOWN pin must not be left floating. If the shutdown feature is unused, the pin may be connected to VDD.

**fault reporting**

The DRV592 includes circuitry to sense three faults:

- Overcurrent
- Undervoltage
- Overtemperature

These three fault conditions are decoded via the FAULT1 and FAULT0 terminals. Internally, these are open-drain outputs, so an external pull-up resistor of 5 k $\Omega$  or greater is required.

**Table 1. Fault Indicators**

FAULT1	FAULT0	
0	0	Overcurrent
0	1	Undervoltage
1	0	Overtemperature
1	1	Normal operation

The over-current fault is reported when the output current exceeds four amps. As soon as the condition is sensed, the over-current fault is set and the outputs go into a high-impedance state for approximately 3  $\mu$ s to 5  $\mu$ s (500 kHz operation). After 3  $\mu$ s to 5  $\mu$ s, the outputs are re-enabled. If the over-current condition has ended, the fault is cleared and the device resumes normal operation. If the over-current condition still exists, the above sequence will repeat.

The under-voltage fault is reported when the operating voltage is reduced below 2.8 V. This fault is not latched, so as soon as the power-supply recovers, the fault is cleared and normal operation resumes. During the under-voltage condition, the outputs are high-impedance to prevent over-dissipation due to increased  $r_{DS(on)}$ .

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## APPLICATION INFORMATION

### fault reporting (continued)

The over-temperature fault is reported when the junction temperature exceeds 130°C. The device continues operating normally until the junction temperature reaches 190°C, at which point the IC is disabled to prevent permanent damage from occurring. The system's controller must reduce the power demanded from the DRV592 once the over-temperature flag is set, or else the device switches off when it reaches 190°C. This flag is not latched, once the junction temperature drops below 130°C, the fault is cleared, and normal operation resumes.

### power dissipation and maximum ambient temperature

Though the DRV592 is much more efficient than traditional linear solutions, the power drop across the on-resistance of the output transistors does generate some heat in the package, which may be calculated as shown in equation (7):

$$P_{DISS} = (I_{OUT})^2 \times r_{DS(on), total} \quad (7)$$

For example, at the maximum output current of 3 A through a total on-resistance of 130 mΩ (at  $T_J = 25^\circ\text{C}$ ), the power dissipated in the package is 1.17 W.

The maximum ambient temperature may be calculated using equation (8):

$$T_A = T_J(\theta_{JA} \times P_{DISS}) \quad (8)$$

### printed circuit board (PCB) layout considerations

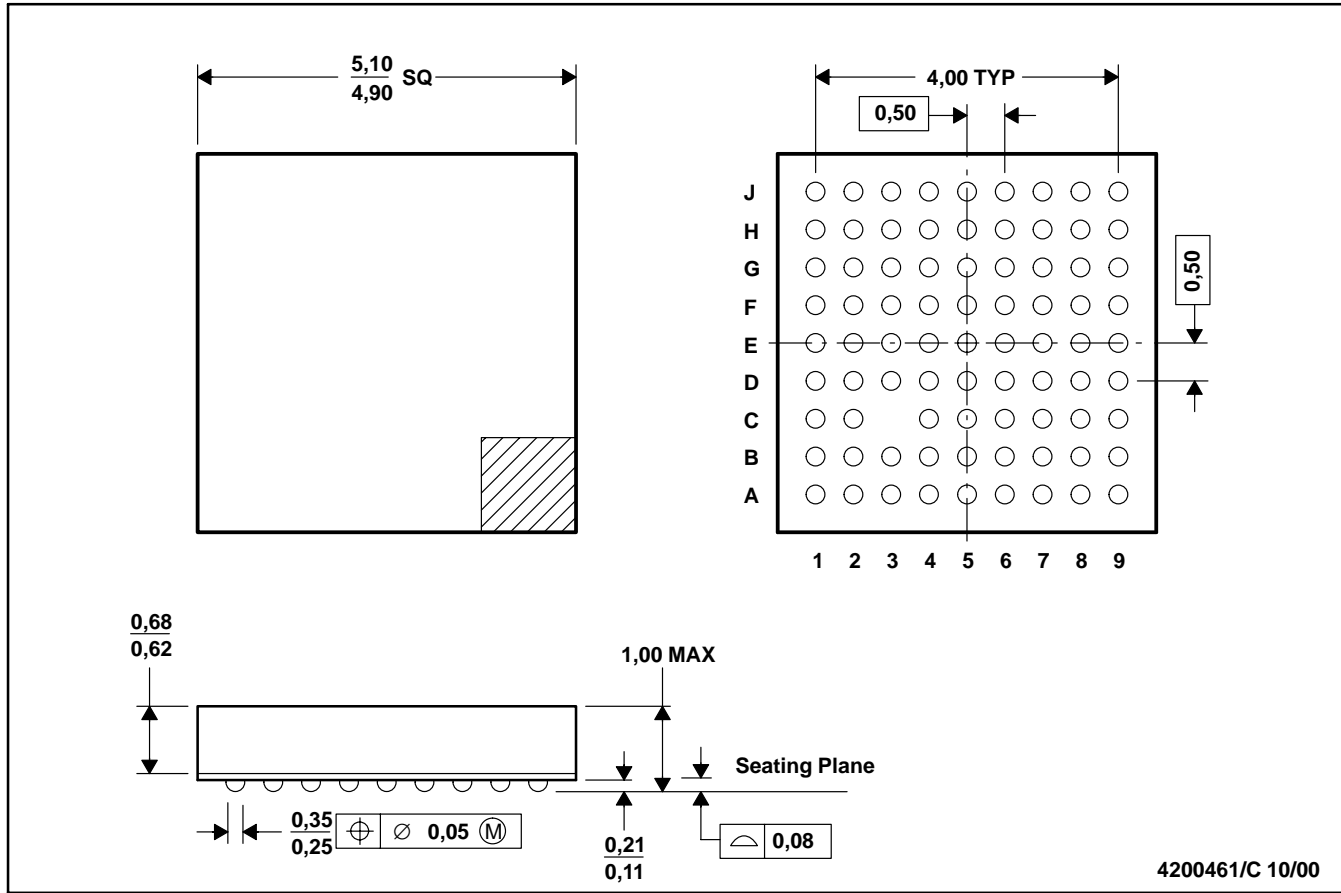
Since the DRV592 is a high-current switching device, a few guidelines for the layout of the printed-circuit board (PCB) must be considered:

1. **Grounding.** Analog ground (AGND) and power ground (PGND) must be kept separated, ideally back to where the power supply physically connects to the PCB, minimally back to the bulk decoupling capacitor (10 μF ceramic minimum). Furthermore, the PowerPAD ground connection should be made to AGND, not PGND. Ground planes are not recommended for AGND or PGND. Wide traces (100 mils) should be used for PGND while narrow traces (15 mils) should be used for AGND.
2. **Power supply decoupling.** A small 0.1-μF to 1-μF ceramic capacitor should be placed as close to each set of PVDD pins as possible, connecting from PVDD to PGND. A 0.1-μF to 1-μF ceramic capacitor should also be placed close to the AVDD pin, connecting from AVDD to AGND. A bulk decoupling capacitor of at least 10 μF, preferably ceramic, should be placed close to the DRV592, from PVDD to PGND.
3. **Power and output traces.** The power and output traces should be sized to handle the desired maximum output current. The output traces should be kept as short as possible to reduce EMI, i.e., the output filter should be placed as close as possible to the DRV592 outputs.
4. **PowerPAD.** The DRV592 in the Quad Flatpack package uses TI's PowerPAD technology to enhance the thermal performance. The PowerPAD is physically connected to the substrate of the DRV592 silicon, which is connected to AGND. The PowerPAD ground connection should therefore be kept separate from PGND as described above. The pad underneath the AGND pin may be connected underneath the device to the PowerPAD ground connection for ease of routing. For additional information on PowerPAD PCB layout, refer to the *PowerPAD Thermally Enhanced Package* application note, TI literature number SLMA002.
5. **Thermal performance.** For proper thermal performance, the PowerPAD must be soldered down to a thermal land, as described in the *PowerPAD Thermally Enhanced Package* application note, TI literature number SLMA002. In addition, at high current levels (greater than 2 A) or high ambient temperatures (greater than 25°C), an internal plane may be used for heat sinking. The vias under the PowerPAD should make a solid connection, and the plane should not be tied to ground except through the PowerPAD connection, as described above.

MECHANICAL DATA

GQE (S-PBGA-N80)

PLASTIC BALL GRID ARRAY



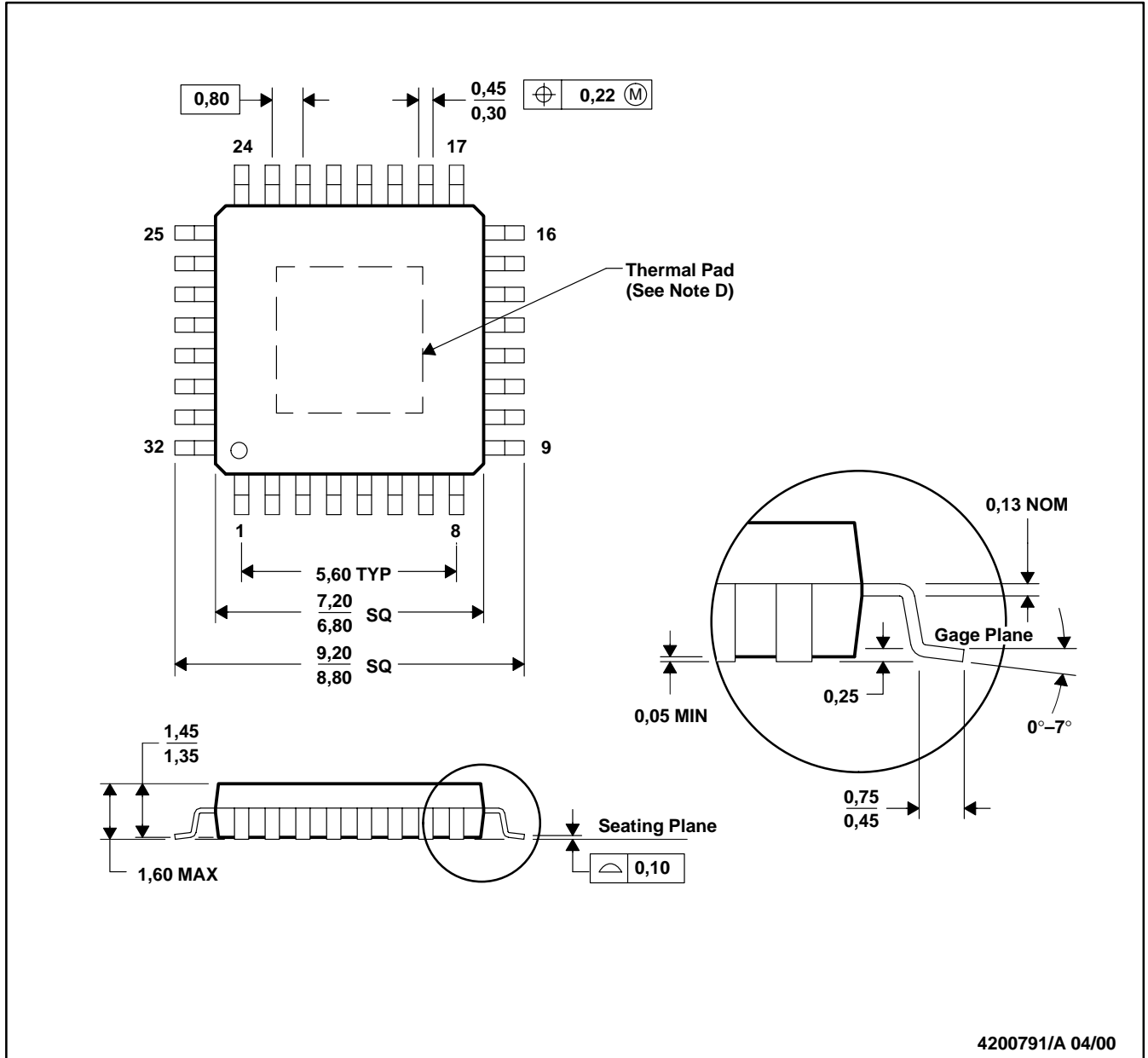
- NOTES: A. All linear dimensions are in millimeters.  
 B. This drawing is subject to change without notice.  
 C. MicroStar Junior™ BGA configuration  
 D. Falls within JEDEC MO-225

MicroStar Junior is a trademark of Texas Instruments.

MECHANICAL DATA

VFP (S-PQFP-G32)

PowerPAD™ PLASTIC QUAD FLATPACK



- NOTES:
- A. All linear dimensions are in millimeters.
  - B. This drawing is subject to change without notice.
  - C. Body dimensions do not include mold flash or protrusion.
  - D. The package thermal performance may be enhanced by bonding the thermal pad to an external thermal plane. This pad is electrically and thermally connected to the backside of the die and possibly selected leads.
  - E. Falls within JEDEC MS-026

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